NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI BLV32F** is Designed for in linear v.h.f. amplifiers of television transmitters and transporters.

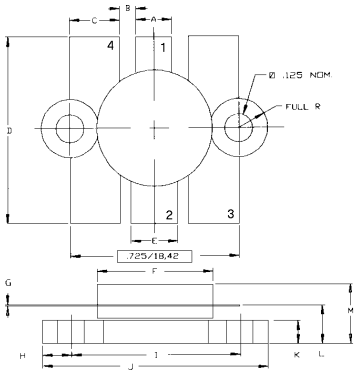
FEATURES:

- Diffused emitter ballasting resistors
- P_G = 16 dB at 10 W/224 MHz
- ***Omnigold***™ Metalization System

MAXIMUM RATINGS

I_C	4.0 A
V_{CBO}	60 V
V_{CEO}	32 V
V_{CES}	60 V
V_{EBO}	4.0 V
P_{DISS}	82 W @ T_C = 25 ^{O}C
T_J	-65 ^{O}C to +200 ^{O}C
T_{STG}	-65 ^{O}C to +150 ^{O}C
θ_{JC}	2.1 ^{O}C/W

PACKAGE STYLE .500 6L FLG



	MINIMUM Inches/mm	MAXIMUM Inches/mm
A	.150/3,43	.160/4,06
B	.045/1,14	
C	.210/5,33	.220/5,59
D	.835/21,21	.865/21,97
E	.200/5,08	.210/5,33
F	.490/12,45	.510/12,95
G	.003/0,08	.007/0,18
H	.125/3,18	
I	.720/18,29	.730/18,54
J	.970/24,64	.980/24,89
K	.095/2,41	.105/2,67
L	.150/3,81	.170/4,32
M		.280/7,11

1= Collector 2= Base 3 and 4= Emitter

CHARACTERISTICS T_C = 25 ^{O}C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I_C = 100 mA	32			V
BV_{CES}	I_C = 15 mA	60			V
BV_{EBO}	I_E = 10 mA	4.0			V
I_{CES}	V_{CE} = 32 V			5.0	mA
h_{FE}	V_{CE} = 25 V I_C = 1.6 A	20		120	---
C_C	V_{CB} = 25 V f = 1.0 MHz		50		pF
P_G	V_{CE} = 25 V P_{OUT} = 10 W f = 224 MHz	16			dB

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